

ABSTRACT

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**Fault Tolerant Magnetoresistive
Solid-state Storage Device**

10 A magnetoresistive solid-state storage device (MRAM)
performs error correction coding (ECC) of stored
information. At manufacture or during use, each logical
block of ECC encoded data and/or the corresponding set of
storage cells are evaluated to determine suitability for
continued use, or whether remedial action is necessary.
15 In a first preferred method ECC decoding is attempted to
determine whether information is unrecoverable from the
block of ECC encoded data. In a second preferred method a
parametric evaluation is made prior to attempting ECC
decoding.

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[Figure 3]

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